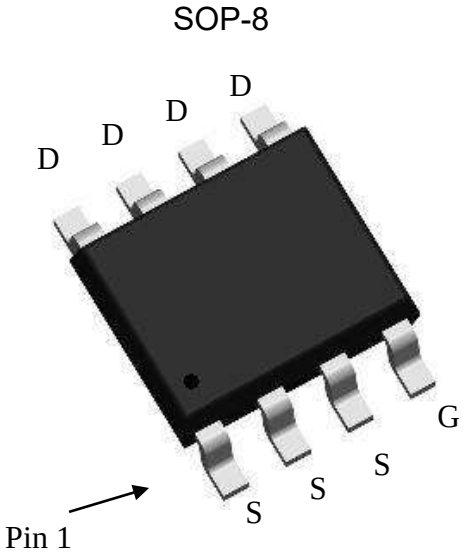
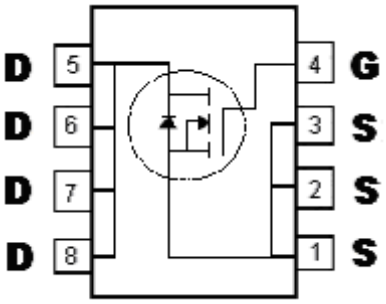
N-Channel Logic Level Enhancement Mode Power MOSFET

Features:

- Single Drive Requirement
- Low On-resistance
- Fast Switching Characteristic
- Repetitive Avalanche Rated
- Pb-free lead plating package



BV_{DSS}	**30V**
I_D@V_{GS}=10V, T_C=25°C	**23A**
R_{DSON}@V_{GS}=10V, I_D=18A	**4.6mΩ(typ)**
R_{DSON}@V_{GS}=4.5V, I_D=12A	**6.5mΩ(typ)**



G：Gate D：Drain S：Source

Ordering Information

Device	Package	Shipping
KSCB06N03	SOP-8 (Pb-free lead plating and halogen-free package)	2500 pcs/ Tape & Reel
KSCB06N03	SOP-8 (Pb-free lead plating and halogen-free package)	4000 pcs/ Tape & Reel

Absolute Maximum Ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current @V_{GS}=10V, T_C=25°C		I_D	23	A
Continuous Drain Current @V_{GS}=10V,T_C=100°C			14	
Continuous Drain Current @V_{GS}=10V,T_A=25°C			16	
Continuous Drain Current @V_{GS}=10V,T_A=100°C			10	
Pulsed Drain Current		I_{DM}	92 *1	
Avalanche Current		I_{AS}	16	
Avalanche Energy @ L=0.1mH, I_D=16A, R_G=25Ω		E_{AS}	12.8	mJ
Repetitive Avalanche Energy @ L=0.05mH		E_{AR}	3 *2	
Total Power Dissipation	T_A=25℃	P_D	2.5	W
	T_A=100℃		1.5	
Operating Junction and Storage Temperature Range		Tj, Tstg	-55~+150	°C

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{th,j-c}$	25	°C/W
Thermal Resistance, Junction-to-ambient, max	$R_{th,j-a}$	50 *3	

Note : 1. Pulse width limited by maximum junction temperature
2. Duty cycle≤1%
3. Surface mounted on 1 in² copper pad of FR-4 board, 125°C/W when mounted on minimum copper pad

Characteristics (T_C=25°C, unless otherwise specified)

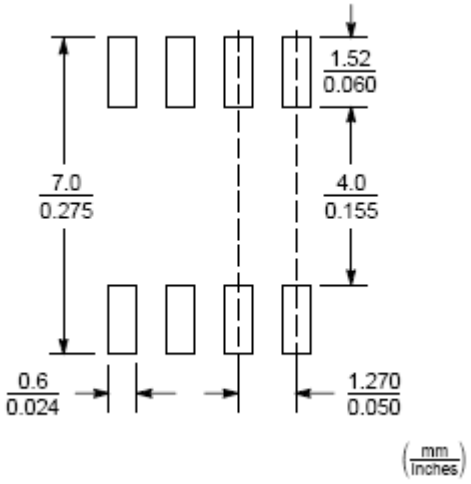
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	30	-	-	V	V_{GS}=0V, I_D=250μA
$V_{GS(th)}$	1.0	-	3.0		V_{DS} = V_{GS}, I_D=250μA
G_{FS} *1	-	20	-	S	V_{DS} =5V, I_D=18A
I_{GSS}	-	-	±100	nA	V_{GS}=±20V
I_{DSS}	-	-	1	μA	V_{DS} =24V, V_{GS} =0V
	-	-	25		V_{DS} =20V, V_{GS} =0V, Tj=125°C
$R_{DS(ON)}$ *1	-	4.6	6	mΩ	V_{GS} =10V, I_D=18A
	-	6.5	8.5		V_{GS} =4.5V, I_D=12A
Dynamic					
Ciss	-	2796	-	pF	V_{GS}=0V, V_{DS}=15V, f=1MHz
Coss	-	308	-		
Crss	-	268	-		

Characteristics (T_C=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Qg (V_{GS}=10V) *1, 2	-	48	-	nC	V_{DS}=15V, V_{GS}=10V, I_D=18A
Qg (V_{GS}=4.5V) *1, 2	-	30	-		
Qgs *1, 2	-	8	-		
Qgd *1, 2	-	17	-		
$t_{d(ON)}$ *1, 2	-	13	-	ns	V_{DS}=15V, I_D=1A, V_{GS}=10V, R_{GS}=2.7Ω
tr *1, 2	-	10	-		
$t_{d(OFF)}$ *1, 2	-	65	-		
t_f *1, 2	-	15	-		
Rg	-	2.8	-	Ω	f=1MHz
Source-Drain Diode					
I_S *1	-	-	4	A	
I_{SM} *3	-	-	40		
V_{SD} *1	-	-	1.2	V	I_F=I_S, V_{GS}=0V
trr	-	28	-	ns	I_F=I_S, dI_F/dt=100A/μs
Qrr	-	12	-	nC	

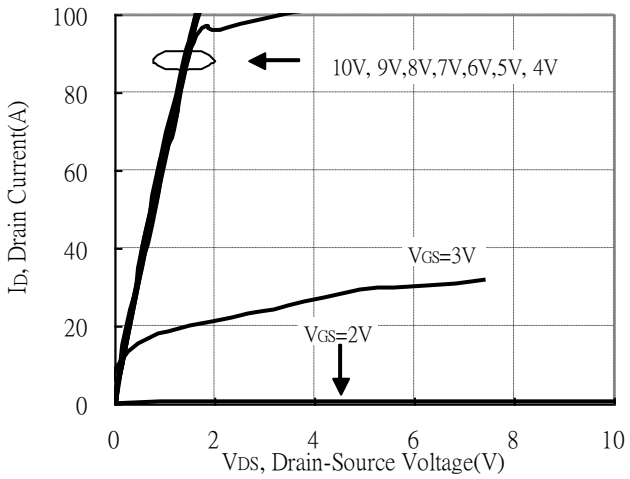
Note : *1.Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%
*2.Independent of operating temperature
*3.Pulse width limited by maximum junction temperature.

Recommended Soldering Footprint

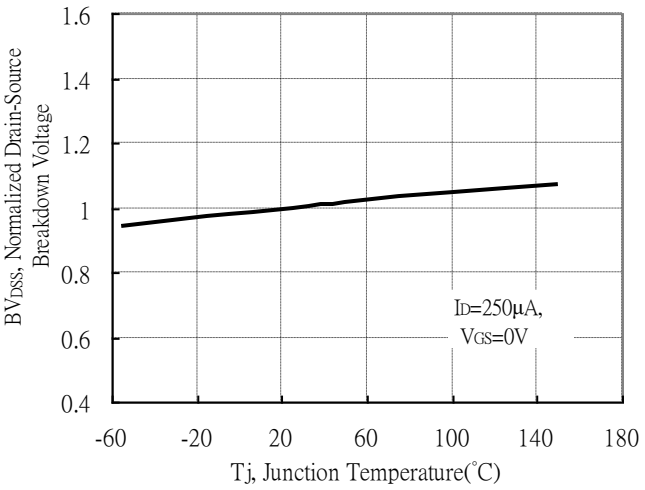


Typical Characteristics

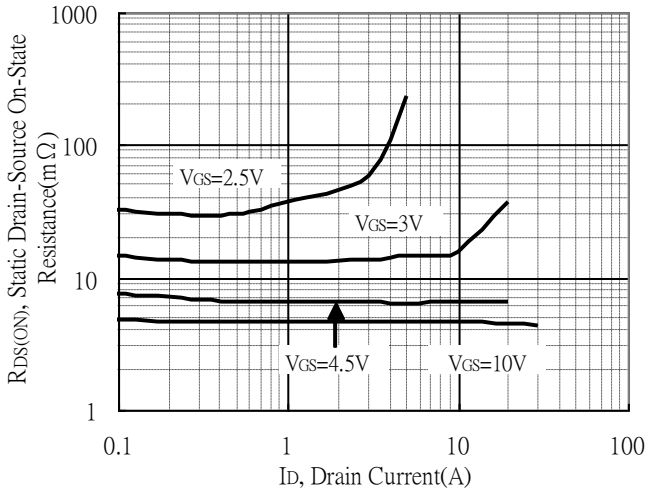
Typical Output Characteristics



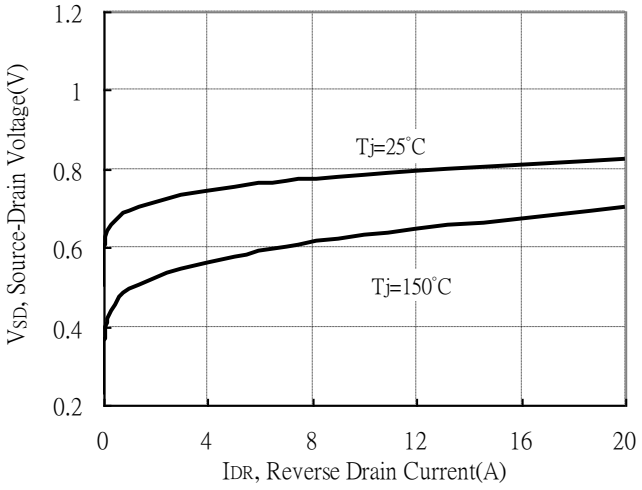
Brekdown Voltage vs Ambient Temperature



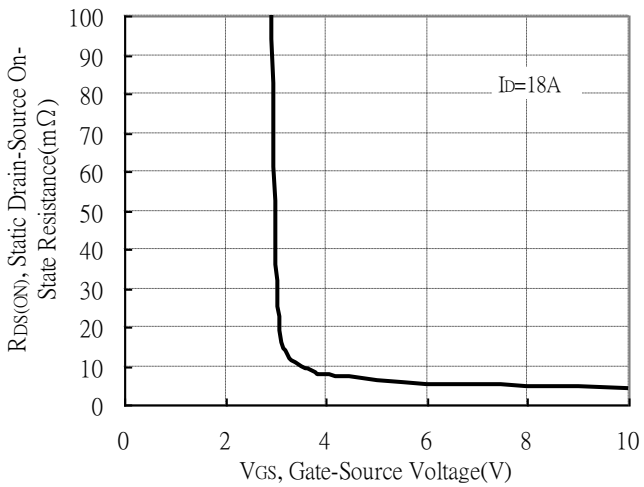
Static Drain-Source On-State resistance vs Drain Current



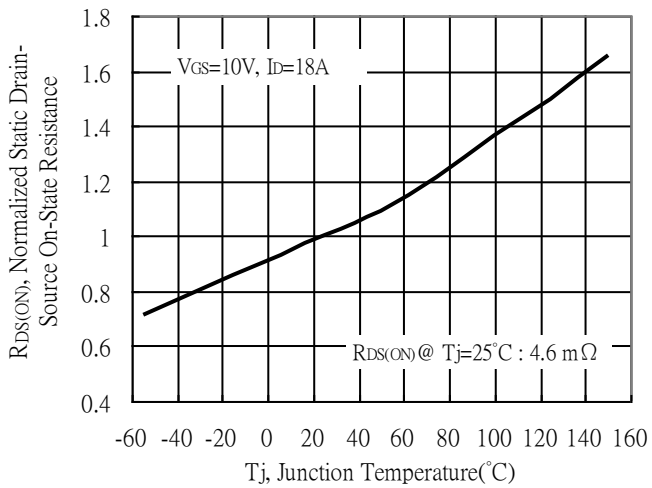
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

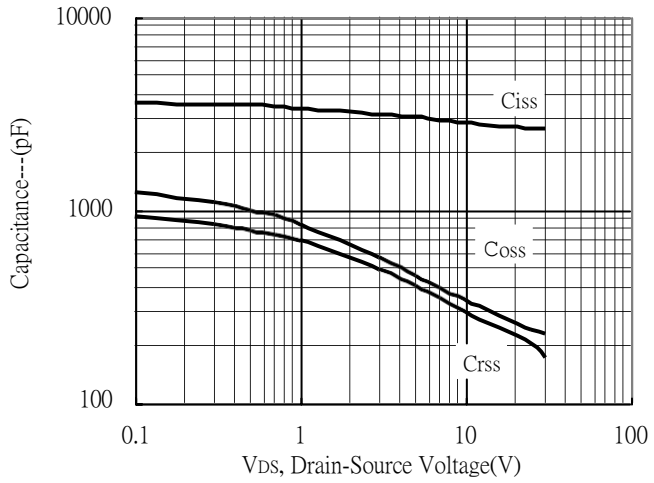


Drain-Source On-State Resistance vs Junction Tempearture

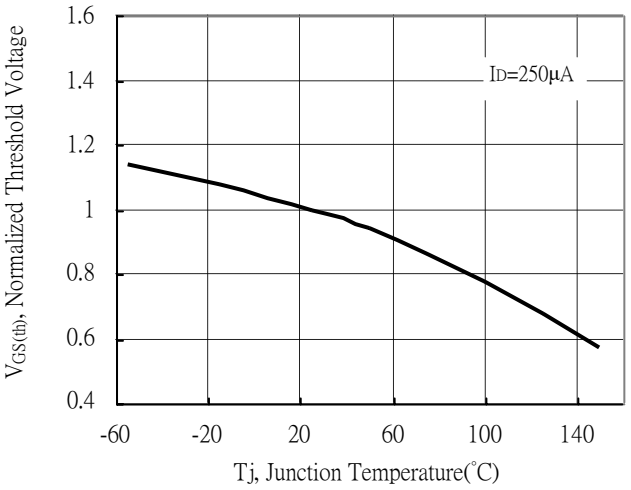


Typical Characteristics(Cont.)

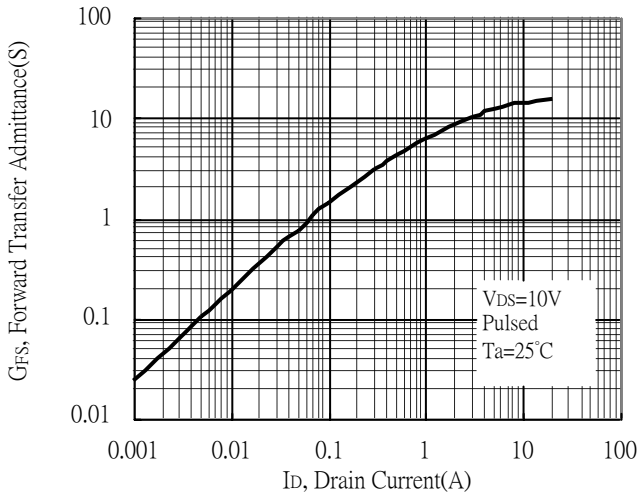
Capacitance vs Drain-to-Source Voltage



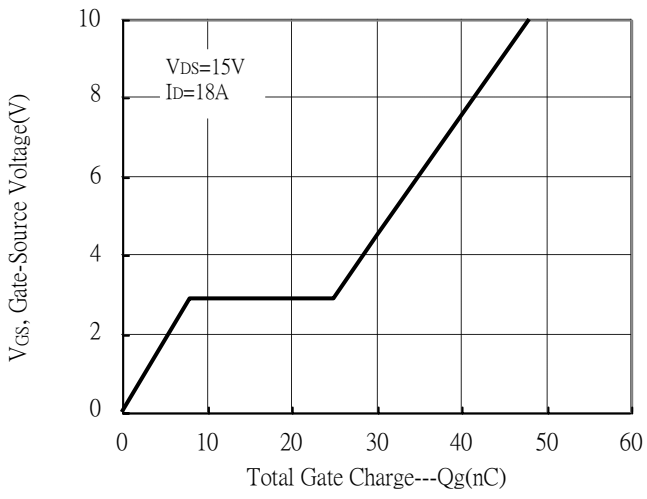
Threshold Voltage vs Junction Tempearture



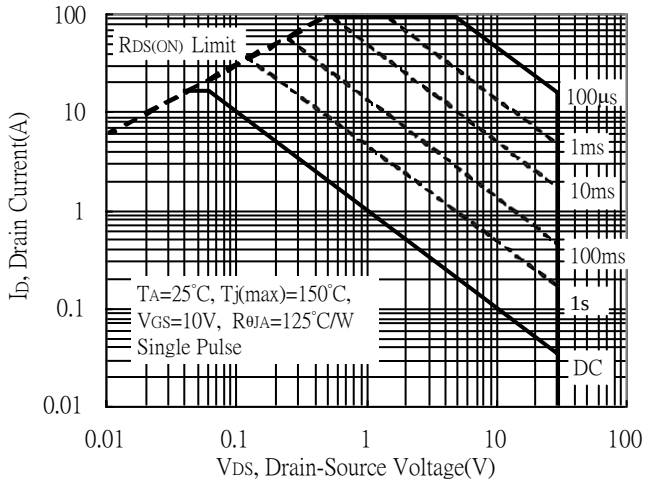
Forward Transfer Admittance vs Drain Current



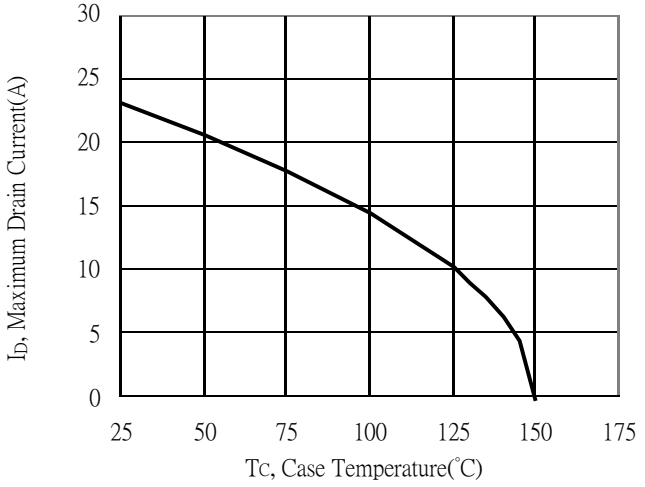
Gate Charge Characteristics



Maximum Safe Operating Area

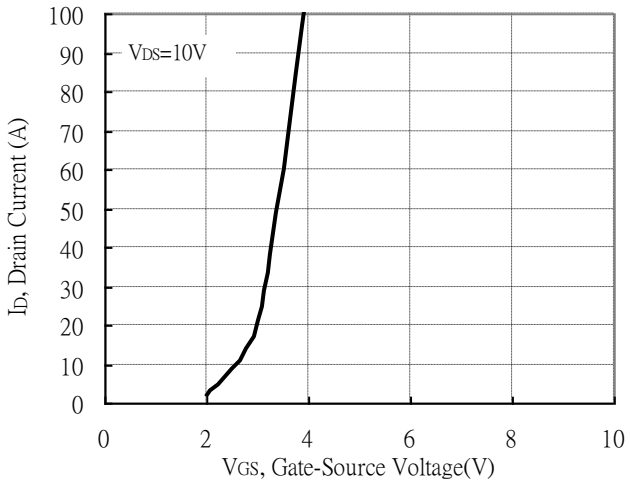


Maximum Drain Current vs Case Temperature

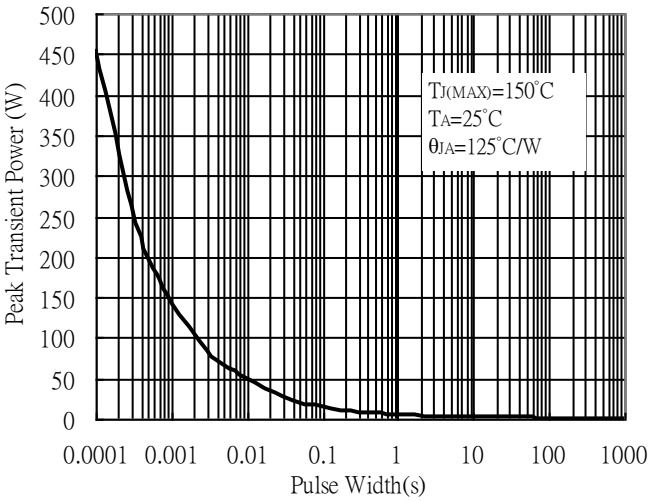


Typical Characteristics(Cont.)

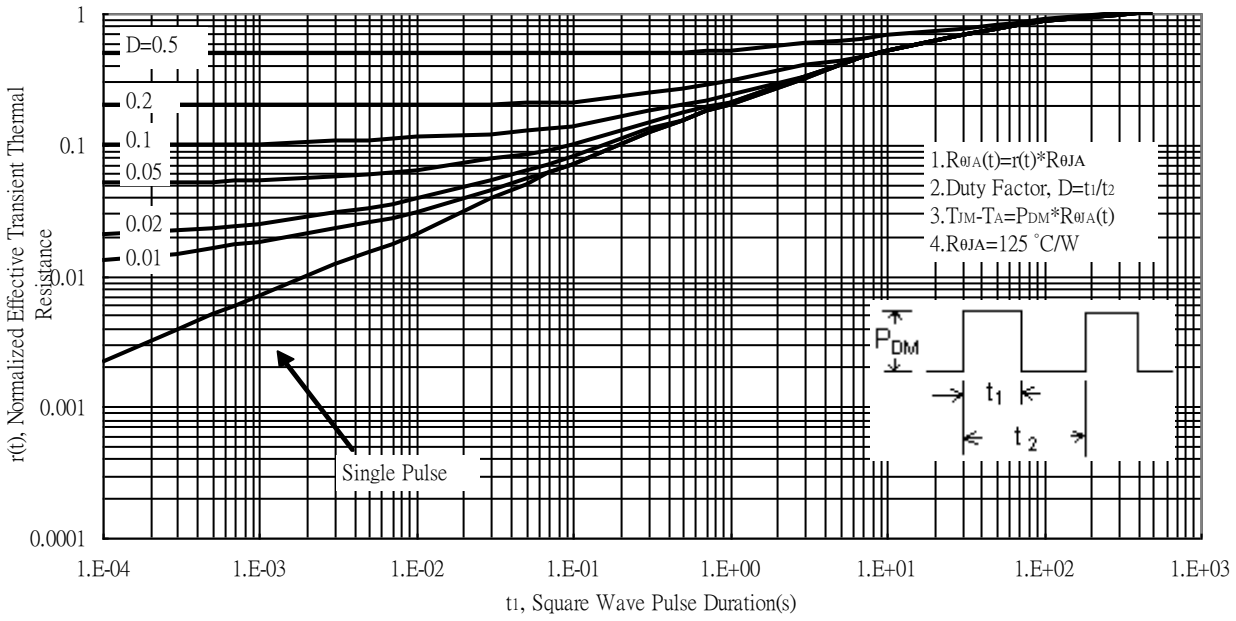
Typical Transfer Characteristics



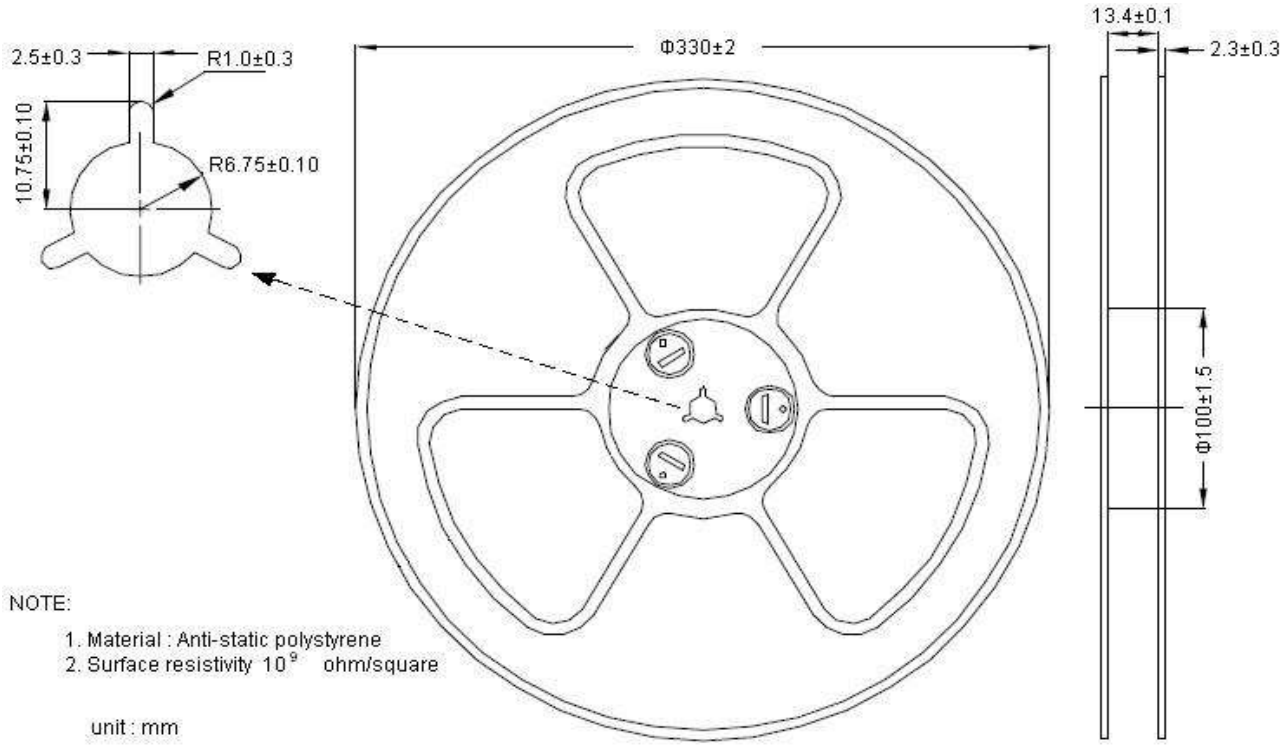
Single Pulse Maximum Power Dissipation



Transient Thermal Response Curves



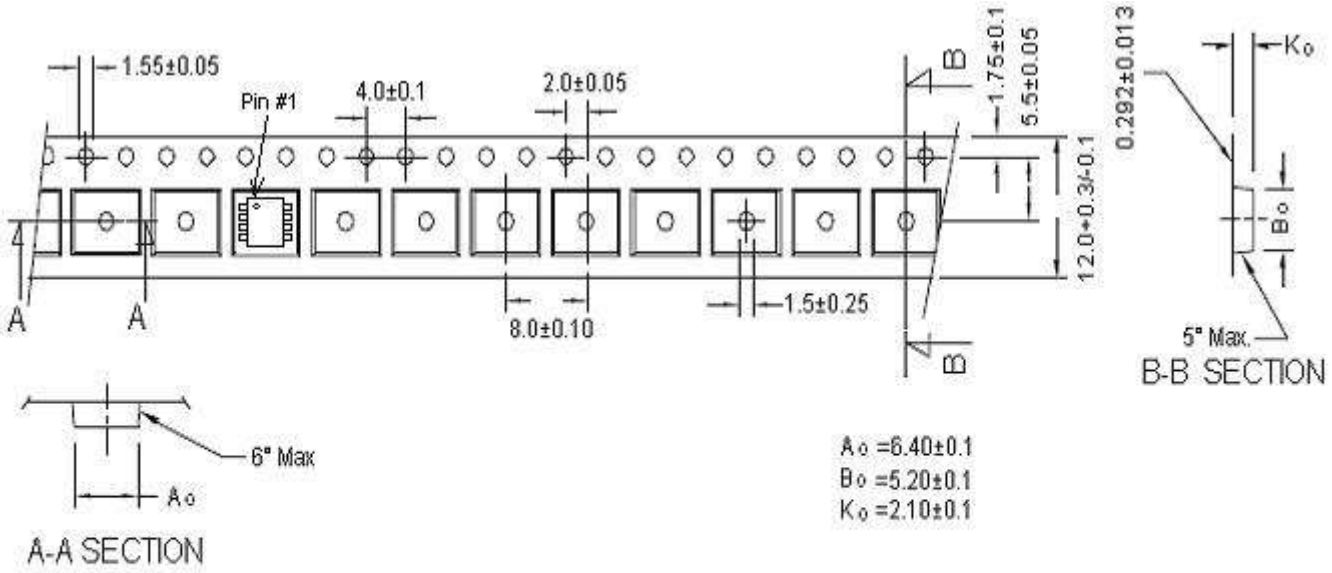
Reel Dimension



NOTE:
1. Material : Anti-static polystyrene
2. Surface resistivity 10^9 ohm/square

unit : mm

Carrier Tape Dimension

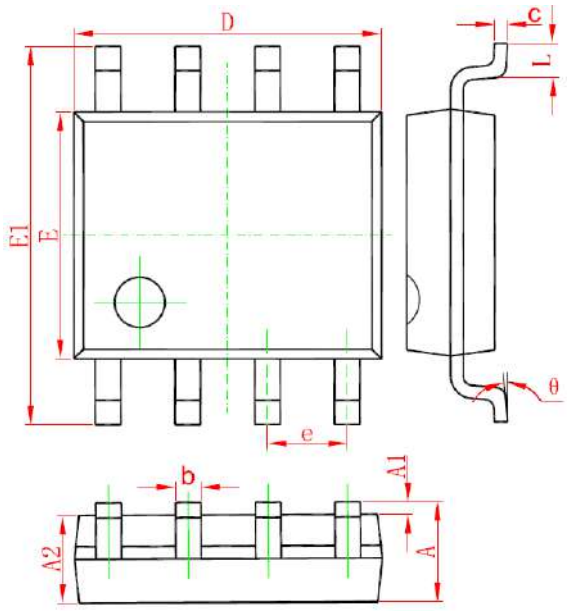


Ao =6.40±0.1
Bo =5.20±0.1
Ko =2.10±0.1

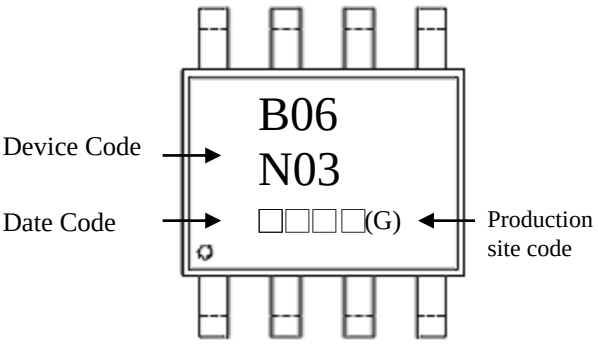
Notes:
1. 10 sprocket hole pitch cumulative tolerance ±0.2.
2. Camber not to exceed 1mm in 100mm.
3. Material: conductive black polystyrene
4. Ao & Bo measured on a plane 0.3mm above the bottom of the pocket.
5. Ko measured from a plane on the inside bottom of the pocket to the top surface of the carrier.
6. Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole.

Uni : millimeter

SOP-8 Dimension



Marking:



Date Code(counting from left to right) :
1st code: year code, the last digit of Christian year
2nd code : month code, Jan→A, Feb→B, Mar→C, Apr→D
May→E, Jun→F, Jul→G, Aug→H, Sep→J,
Oct→K, Nov→L, Dec→M
3rd and 4th codes : production serial number, 01~99

Production site code : blank→ JCET, G →GEM

8-Lead SOP-8 Plastic Package

*: Typical

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069	E	3.800	4.000	0.150	0.157
A1	0.100	0.250	0.004	0.010	E1	5.800	6.200	0.228	0.244
A2	1.350	1.550	0.053	0.061	e	*1.270		*0.050	
b	0.330	0.510	0.013	0.020	L	0.400	1.270	0.016	0.050
c	0.170	0.250	0.006	0.010	θ	0°	8°	0°	8°
D	4.700	5.100	0.185	0.200					